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## Low Dropout Linear Voltage Regulator

## TLS850D0TE

TLS850D0TEV50

TLS850D0TEV33

## Linear Voltage Regulator

## **Data Sheet**

Rev. 1.0, 2016-10-07

**Automotive Power** 



## **Table of Contents**

## **Table of Contents**

1	Overview
2	Block Diagram 5
<b>3</b> 3.1 3.2	Pin Configuration6Pin Assignment TLS850D0TEV50 and TLS850D0TEV336Pin Definitions and Functions TLS850D0TEV50 and TLS850D0TEV336
<b>4</b> 4.1 4.2 4.3	General Product Characteristics7Absolute Maximum Ratings7Functional Range8Thermal Resistance9
<b>5</b> 5.1 5.2 5.3 5.4 5.5 5.6 5.7 5.8	Block Description and Electrical Characteristics10Voltage Regulation10Typical Performance Characteristics Voltage Regulator13Current Consumption16Typical Performance Characteristics Current Consumption17Enable18Typical Performance Characteristics Enable19Reset20Typical Performance Characteristics Reset23
6 6.1 6.2 6.2.1 6.2.2 6.3 6.4 6.5	Application Information       24         Application Diagram       24         Selection of External Components       24         Input Pin       24         Output Pin       24         Thermal Considerations       25         Reverse Polarity Protection       26         Further Application Information       26
7	Package Outlines
8	Revision History



## **Low Dropout Linear Voltage Regulator**

## TLS850D0TE





## 1 Overview

#### **Features**

- Wide Input Voltage Range from 3.0 V to 40 V
- Fixed Output Voltage 5 V or 3.3 V
- Output Voltage Precision ≤ ±2 %
- · Output Current Capability up to 500 mA
- Ultra Low Current Consumption typ. 40 μA
- Very Low Dropout Voltage typ. 70 mV @100 mA
- Stable with Ceramic Output Capacitor of 1 µF
- · Delayed Reset at Power-On: 16.5 ms
- Enable, Undervoltage Reset, Overtemperature Shutdown
- · Output Current Limitation
- · Wide Temperature Range
- Green Product (RoHS compliant)
- AEC Qualified



Figure 1 PG-TO252-5



Overview

## **Functional Description**

The TLS850D0TE is a high performance very low dropout linear voltage regulator for 5 V (TLS850D0V50) or 3.3 V (TLS850D0V33) supply in a PG-TO252-5 package.

With an input voltage range of 3 V to 40 V and very low quiescent of only 40  $\mu$ A, these regulators are perfectly suitable for automotive or any other supply systems connected to the battery permanently. The TLS850D0TE provides an output voltage accuracy of 2 % and a maximum output current up to 500 mA.

The new loop concept combines fast regulation and very good stability while requiring only one small ceramic capacitor of 1  $\mu$ F at the output. At currents below 100 mA the device will have a very low typical dropout voltage of only 70 mV (for 5 V device) and 80 mV (for 3.3 V device). The operating range starts already at input voltages of only 3 V (extended operating range). This makes the TLS850D0TE also suitable to supply automotive systems that need to operate during cranking condition.

The device can be switched on and off by the Enable feature as described in Chapter 5.5.

The output voltage is supervised by the Reset feature, including Undervoltage Reset and delayed Reset at Power-On, more details can be found in **Chapter 5.7**.

Internal protection features like output current limitation and overtemperature shutdown are implemented to protect the device against immediate damage due to failures like output short circuit to GND, over-current and over-temperatures.

## **Choosing External Components**

An input capacitor  $C_1$  is recommended to compensate line influences. The output capacitor  $C_Q$  is necessary for the stability of the regulating circuit. TLS850D0TE is designed to be also stable with low ESR ceramic capacitors.

Туре	Package	Marking	
TLS850D0TEV50	PG-TO252-5	850D0V50	
TLS850D0TEV33	PG-TO252-5	850D0V33	

Data Sheet 4 Rev. 1.0, 2016-10-07



**Block Diagram** 

## 2 Block Diagram

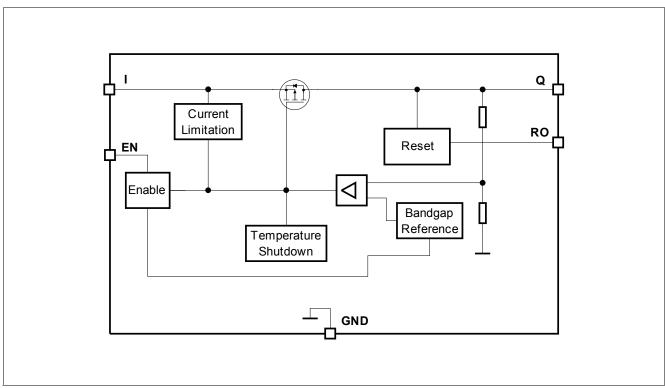


Figure 2 Block Diagram TLS850D0TEV50 and TLS850D0TEV33



**Pin Configuration** 

## 3 Pin Configuration

## 3.1 Pin Assignment TLS850D0TEV50 and TLS850D0TEV33

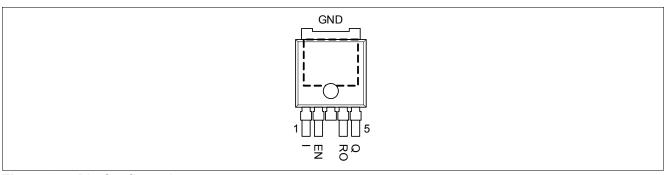


Figure 3 Pin Configuration

## 3.2 Pin Definitions and Functions TLS850D0TEV50 and TLS850D0TEV33

Pin	Symbol	Function
1	I	Input
		It is recommended to place a small ceramic capacitor (e.g. 100 nF) to GND, close to the IC terminals, in order to compensate line influences. See also <b>Chapter 6.2.1</b>
2	EN	Enable (integrated pull-down resistor)
		Enable the IC with high level input signal;
		Disable the IC with low level input signal;
3	GND	Ground
4	RO	Reset Output (intergrated pull-up resistor to Q)
		Open collector output;
		Leave open if the reset function is not needed
5	Q	Output Voltage
		Connect output capacitor $C_{\rm Q}$ to GND close to the IC's terminals, respecting the
		values specified for its capacitance and ESR in "Functional Range" on Page 8
Heat	GND	Heat Slug
Slug		Connect to GND
		Connect to heatsink area;



**General Product Characteristics** 

## 4 General Product Characteristics

## 4.1 Absolute Maximum Ratings

## Table 1 Absolute Maximum Ratings<sup>1)</sup>

 $T_i$  = -40 °C to +150 °C; all voltages with respect to ground (unless otherwise specified)

Parameter	Symbol		Value	S	Unit	Note /	Number
		Min.	Тур.	Max.		<b>Test Condition</b>	
Input I, Enable EN	1		•				
Voltage	$V_{I},V_{EN}$	-0.3	_	45	V	_	P_4.1.1
Output Q, Reset Output RO		- 1	"				
Voltage	$V_{\rm Q},V_{\rm RO}$	-0.3	_	7	V	_	P_4.1.3
Temperatures	!				-	,	<del>'</del>
Junction Temperature	$T_{\rm j}$	-40	_	150	°C	_	P_4.1.7
Storage Temperature	$T_{\rm stg}$	-55	_	150	°C	_	P_4.1.8
ESD Absorption			•				
ESD Susceptibility to GND	$V_{ESD}$	-2	_	2	kV	<sup>2)</sup> HBM	P_4.1.9
ESD Susceptibility to GND	$V_{ESD}$	-500	_	500	V	3) CDM	P_4.1.10
ESD Susceptibility Pin 1, 5 (corner pins) to GND	$V_{\mathrm{ESD1,5}}$	-750	_	750	V	3) CDM	P_4.1.13

<sup>1)</sup> Not subject to production test, specified by design.

#### Note:

- 1. Stresses above the ones listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.
- 2. Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.

Data Sheet 7 Rev. 1.0, 2016-10-07

<sup>2)</sup> ESD susceptibility, HBM according to ANSI/ESDA/JEDEC JS001 (1.5 kΩ, 100 pF)

<sup>3)</sup> ESD susceptibility, Charged Device Model "CDM" according JEDEC JESD22-C101



#### **General Product Characteristics**

## 4.2 Functional Range

Table 2 Functional Range

 $T_i$  = -40 °C to +150 °C; all voltages with respect to ground (unless otherwise specified)

Parameter	Symbol	V	alues		Unit	Note / Test Condition	Number
		Min.	Тур.	Max.			
Input Voltage Range	$V_1$	$V_{\rm Q,nom}$ + $V_{\rm dr}$	_	40	V	1) _	P_4.2.1
Extended Input Voltage Range	$V_{I,ext}$	3.0	_	40	V	2)	P_4.2.3
Enable Voltage Range	$V_{EN}$	0	_	40	V	_	P_4.2.5
Output Capacitor's	$C_{Q}$	1	_	_	μF	3)4) _	P_4.2.6
Requirements for Stability							
ESR	$ESR(C_{Q})$	_	_	100	Ω	3) _	P_4.2.7
Junction Temperature	$T_{i}$	-40	_	150	°C	_	P_4.2.9

<sup>1)</sup> Output current is limited internaly and depends on the input voltage, see Electrical Characteristics for more details.

Note: Within the functional or operating range, the IC operates as described in the circuit description. The electrical characteristics are specified within the conditions given in the Electrical Characteristics table.

Data Sheet 8 Rev. 1.0, 2016-10-07

<sup>2)</sup> When  $V_{\rm l}$  is between  $V_{\rm l,ext,min}$  and  $V_{\rm Q,nom}$  +  $V_{\rm dr}$ ,  $V_{\rm Q}$  =  $V_{\rm l}$  -  $V_{\rm dr}$ . When  $V_{\rm l}$  is below  $V_{\rm l,ext,min}$ ,  $V_{\rm Q}$  can drop down to 0 V.

<sup>3)</sup> Not subject to production test, specified by design.

<sup>4)</sup> The minimum output capacitance requirement is applicable for a worst case capacitance tolerance of 30%



#### **General Product Characteristics**

## 4.3 Thermal Resistance

Note: This thermal data was generated in accordance with JEDEC JESD51 standards. For more information, go to www.jedec.org.

Table 3 Thermal Resistance

Parameter	Symbol		Value	S	Unit	Note / Test Condition	Number
		Min.	Тур.	Max.			
Package Version PG-TO25	52-5	-1				•	
Junction to Case	$R_{thJC}$	_	3	_	K/W	1) _	P_4.3.11
Junction to Ambient	$R_{thJA}$	_	26	_	K/W	<sup>1)2)</sup> 2s2p board	P_4.3.12
Junction to Ambient	$R_{thJA}$	_	109	_	K/W	1)3) 1s0p board, footprint only	P_4.3.13
Junction to Ambient	$R_{thJA}$	-	51	-	K/W	1)3) 1s0p board, 300 mm² heatsink area on PCB	P_4.3.14
Junction to Ambient	$R_{thJA}$	-	40	-	K/W	1)3) 1s0p board, 600 mm <sup>2</sup> heatsink area on PCB	P_4.3.15

<sup>1)</sup> Not subject to production test, specified by design

Data Sheet 9 Rev. 1.0, 2016-10-07

<sup>2)</sup> Specified R<sub>thJA</sub> value is according to Jedec JESD51-2,-5,-7 at natural convection on FR4 2s2p board; The Product (Chip+Package) was simulated on a 76.2 x 114.3 x 1.5 mm³ board with 2 inner copper layers (2 x 70μm Cu, 2 x 35μm Cu). Where applicable a thermal via array under the exposed pad contacted the first inner copper layer.

<sup>3)</sup> Specified  $R_{\text{thJA}}$  value is according to JEDEC JESD 51-3 at natural convection on FR4 1s0p board; The Product (Chip+Package) was simulated on a 76.2 × 114.3 × 1.5 mm<sup>3</sup> board with 1 copper layer (1 x 70 $\mu$ m Cu).



## 5 Block Description and Electrical Characteristics

## 5.1 Voltage Regulation

The output voltage  $V_Q$  is divided by a resistor network. This fractional voltage is compared to an internal voltage reference and the pass transistor is driven accordingly.

The control loop stability depends on the output capacitor  $C_{\rm Q}$ , the load current, the chip temperature and the internal circuit design. To ensure stable operation, the output capacitor's capacitance and its equivalent series resistor (ESR) requirements given in "Functional Range" on Page 8 have to be maintained. For details, also see the typical performance graph "Output Capacitor Series Resistor ESR(CQ) versus Output Current IQ" on Page 15. As the output capacitor also has to buffer load steps, it should be sized according to the application's needs.

An input capacitor  $C_1$  is recommended to compensate line influences. In order to block influences like pulses and HF distortion at input side, an additional reverse polarity protection diode and a combination of several capacitors for filtering should be used. Connect the capacitors close to the component's terminals.

In order to prevent overshoots during start-up, a smooth ramp up function is implemented. This ensures almost no output voltage overshoots during start-up, mostly independent from load and output capacitance.

Whenever the load current exceeds the specified limit, e.g. in case of a short circuit, the output current is limited and the output voltage decreases.

The overtemperature shutdown circuit prevents the IC from immediate destruction under fault conditions (e.g. output continuously short-circuit) by switching off the power stage. After the chip has cooled down, the regulator restarts. This leads to an oscillatory behavior of the output voltage until the fault is removed. However, junction temperatures above 150 °C are outside the maximum ratings and therefore significantly reduce the IC's lifetime.

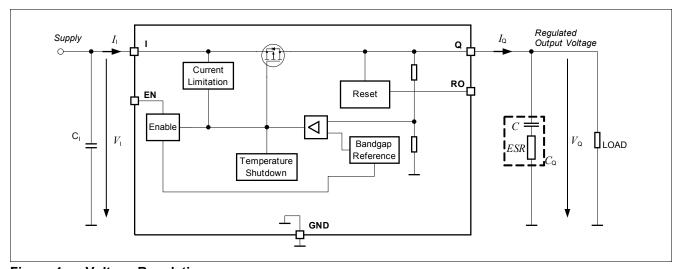


Figure 4 Voltage Regulation

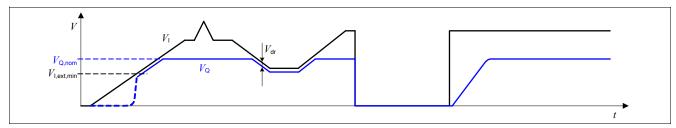


Figure 5 Output Voltage vs. Input Voltage



## Table 4 Electrical Characteristics Voltage Regulator 5 V version

 $T_{\rm j}$  = -40 °C to +150 °C,  $V_{\rm l}$  = 13.5 V, all voltages with respect to ground (unless otherwise specified) Typical values are given at  $T_{\rm j}$  = 25 °C

Parameter	Symbol	Values			Unit	Note / Test Condition	Number
		Min.	Тур.	Max.			
Output Voltage Precision	$V_{Q}$	4.9	5.0	5.1	V	$0.05 \text{ mA} < I_{\text{Q}} < 500 \text{ mA}$ $5.95 \text{ V} < V_{\text{I}} < 28 \text{ V}$	P_5.1.3
Output Voltage Precision	$V_{Q}$	4.9	5.0	5.1	V	$0.05 \text{ mA} < I_{\text{Q}} < 200 \text{ mA}$ $5.44 \text{ V} < V_{\text{I}} < 40 \text{ V}$	P_5.1.4
Output Voltage Start-up slew rate	$\mathrm{d}V_{\mathrm{Q}}/\mathrm{dt}$	3.0	7.5	18	V/ms	$V_I > 18 \text{ V/ms}$ $C_Q = 1 \mu\text{F}$ $0.5 \text{ V} < V_Q < 4.5 \text{ V}$	P_5.1.7
Output Current Limitation	$I_{Q,max}$	501	650	1100	mA	0 V < V <sub>Q</sub> < 4.8 V	P_5.1.9
Load Regulation steady-state	$\Delta V_{ m Q,load}$	-20	-1.5	5	mV	$I_{\rm Q}$ = 0.05 mA to 500 mA $V_{\rm I}$ = 6 V	P_5.1.11
Line Regulation steady-state	$\Delta V_{ m Q,line}$	-20	0	20	mV	$V_{\rm I}$ = 8 V to 32 V $I_{\rm Q}$ = 5 mA	P_5.1.13
Dropout Voltage $V_{dr} = V_1 - V_Q$	$V_{dr}$	-	175	425	mV	<sup>1)</sup> $I_{\rm Q}$ = 250 mA	P_5.1.16
Dropout Voltage $V_{dr} = V_1 - V_Q$	$V_{dr}$	-	70	170	mV	$I_{\rm Q}$ = 100 mA	P_5.1.17
Power Supply Ripple Rejection	PSRR	_	59	_	dB	$V_{\text{ripple}}^{(2)} = 100 \text{ Hz}$ Hz $V_{\text{ripple}}^{(2)} = 0.5 \text{ Vpp}$	P_5.1.18
Overtemperature Shutdown Threshold	$T_{ m j,sd}$	151	-	200	°C	$^{2)}$ $T_{\rm j}$ increasing	P_5.1.19
Overtemperature Shutdown Threshold Hysteresis	$T_{ m j,sdh}$	_	15	-	K	$^{2)}$ $T_{\rm j}$ decreasing	P_5.1.20

<sup>1)</sup> Measured when the output voltage  $V_{\rm Q}$  has dropped 100 mV from the nominal value obtained at  $V_{\rm I}$  = 13.5V

<sup>2)</sup> Not subject to production test, specified by design



## Table 5 Electrical Characteristics Voltage Regulator 3.3 V version

 $T_{\rm j}$  = -40 °C to +150 °C,  $V_{\rm l}$  = 13.5 V, all voltages with respect to ground (unless otherwise specified) Typical values are given at  $T_{\rm j}$  = 25 °C

Parameter	Symbol		Values	<b>3</b>	Unit	Note / Test Condition	Number
		Min.	Тур.	Max.			
Output Voltage Precision	$V_{Q}$	3.23	3.3	3.37	V	$0.05 \text{ mA} < I_{\text{Q}} < 500 \text{ mA}$ $4.23 \text{ V} < V_{\text{I}} < 28 \text{ V}$	P_5.1.23
Output Voltage Precision	$V_{Q}$	3.23	3.3	3.37	V	$0.05 \text{ mA} < I_{\text{Q}} < 200 \text{ mA}$ $3.72 \text{ V} < V_{\text{I}} < 40 \text{ V}$	P_5.1.24
Output Voltage Start-up slew rate	$\mathrm{d}V_{\mathrm{Q}}/\mathrm{dt}$	3.0	7.5	18	V/ms	$V_I > 18 \text{ V/ms}$ $C_Q = 1 \mu\text{F}$ $0.33 \text{ V} < V_Q < 2.97 \text{ V}$	P_5.1.27
Output Current Limitation	$I_{Q,max}$	501	650	1100	mA	0 V < V <sub>Q</sub> < 3.1 V	P_5.1.29
Load Regulation steady-state	$\Delta V_{ m Q,load}$	-20	-1.5	5	mV	$I_{\rm Q}$ = 0.05 mA to 500 mA $V_{\rm I}$ = 6 V	P_5.1.31
Line Regulation steady-state	$\Delta V_{ m Q,line}$	-15	0	15	mV	$V_{\rm I}$ = 8 V to 32 V $I_{\rm Q}$ = 5 mA	P_5.1.33
Dropout Voltage $V_{dr} = V_1 - V_Q$	$V_{dr}$	_	200	430	mV	<sup>1)</sup> $I_{\rm Q}$ = 250 mA	P_5.1.36
Dropout Voltage $V_{dr} = V_1 - V_Q$	$V_{dr}$	_	80	175	mV	<sup>I)</sup> I <sub>Q</sub> = 100 mA	P_5.1.37
Power Supply Ripple Rejection	PSRR	_	63	_	dB	$V_{\text{ripple}}^{(2)} = 100 \text{ Hz}$ $V_{\text{ripple}}^{(2)} = 0.5 \text{ Vpp}$	P_5.1.38
Overtemperature Shutdown Threshold	$T_{ m j,sd}$	151	-	200	°C	$^{2)}$ $T_{\rm j}$ increasing	P_5.1.39
Overtemperature Shutdown Threshold Hysteresis	$T_{ m j,sdh}$	_	15	_	K	$^{2)}$ $T_{\rm j}$ decreasing	P_5.1.40

<sup>1)</sup> Measured when the output voltage  $V_{\rm Q}$  has dropped 100 mV from the nominal value obtained at  $V_{\rm I}$  = 13.5V

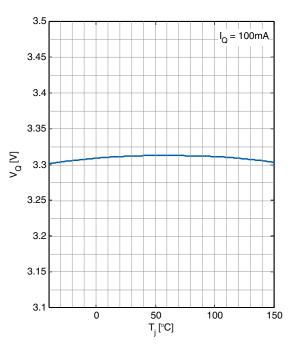
<sup>2)</sup> Not subject to production test, specified by design



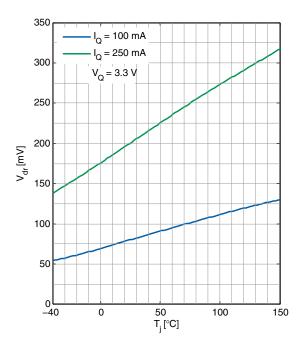
## 5.2 Typical Performance Characteristics Voltage Regulator

## **Typical Performance Characteristics**

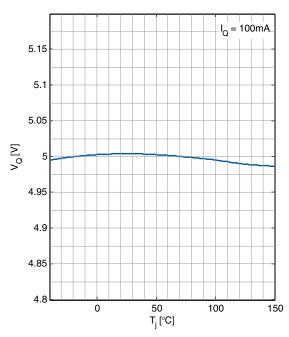
## Output Voltage $V_{\rm Q}$ versus Junction Temperature $T_{\rm i}$ (3.3 V version)



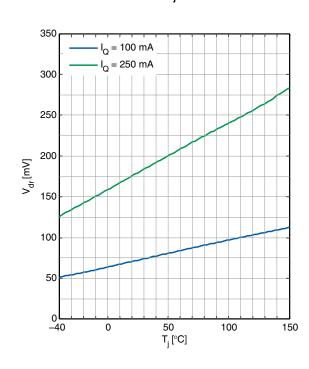
Dropout Voltage  $V_{\rm dr}$  versus Junction Temperature  $T_{\rm i}$  (3.3 V version)



# Output Voltage $V_{\rm Q}$ versus Junction Temperature $T_{\rm i}$ (5 V version)

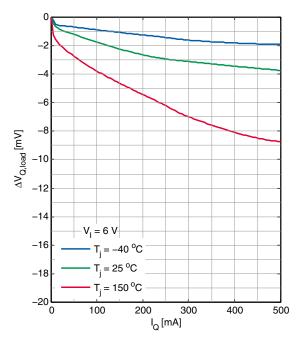


Dropout Voltage  $V_{\rm dr}$  versus Junction Temperature  $T_{\rm i}$  (5 V version)

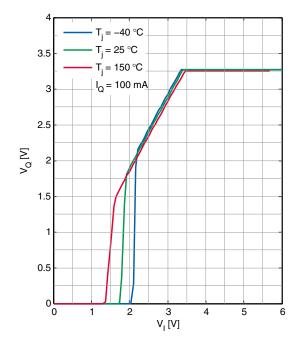




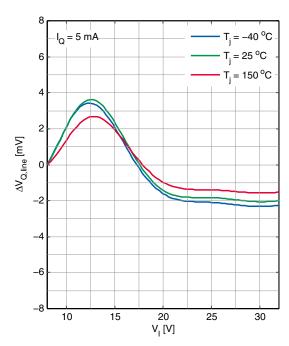
# Load Regulation $\Delta V_{\rm Q,load}$ versus Output Current Change $I_{\rm Q}$



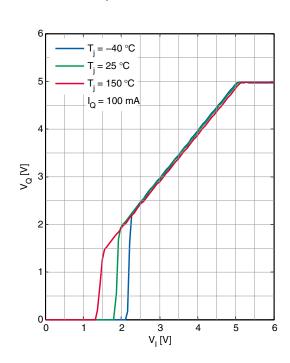
Output Voltage  $V_{\rm Q}$  versus Input Voltage  $V_{\rm I}$  (3.3 V version)



Line Regulation  $\Delta V_{
m Q,line}$  versus Input Voltage  $V_{
m I}$ 

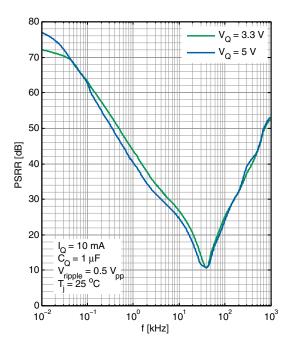


Output Voltage  $V_{\rm Q}$  versus Input Voltage  $V_{\rm I}$  (5 V version)

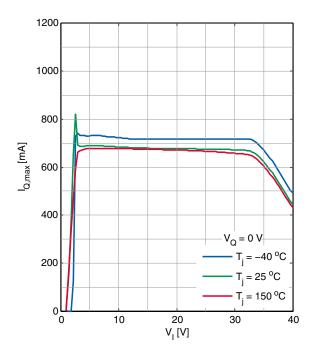




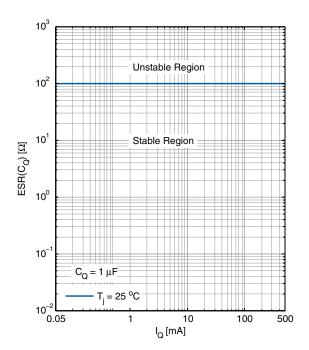
## Power Supply Ripple Rejection PSRR versus ripple frequency f



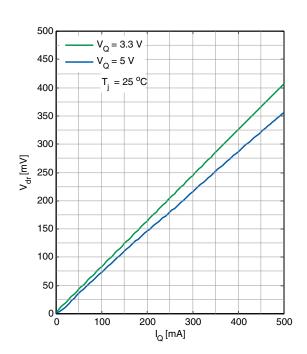
## Maximum Output Current $I_{\mathsf{Q}}$ versus Input Voltage $V_{\mathsf{I}}$



## Output Capacitor Series Resistor $ESR(C_{\rm Q})$ versus Output Current $I_{\rm Q}$



Dropout Voltage  $V_{\mathrm{dr}}$  versus Output Current  $I_{\mathrm{O}}$ 





## 5.3 Current Consumption

## Table 6 Electrical Characteristics Current Consumption

 $T_{\rm j}$  = -40 °C to +150 °C,  $V_{\rm l}$  = 13.5 V (unless otherwise specified) Typical values are given at  $T_{\rm i}$  = 25 °C

Parameter	Symbol	l Values			Unit	Note / Test Condition	Number
		Min.	Min. Typ. Max.				
Current Consumption	$I_{q,off}$	_	1.3	5	μΑ	$V_{\rm EN}$ = 0 V; $T_{\rm i}$ < 105 °C	P_5.3.1
$I_{q} = I_{l}$	4,					,	
Current Consumption	$I_{q,off}$	_	-	8	μΑ	$V_{\rm EN}$ = 0.4 V; $T_{\rm j}$ < 125 °C	P_5.3.3
$I_{q} = I_{l}$						,	
Current Consumption	$I_{q}$	_	40	52	μΑ	$I_{\rm Q}$ = 0.05 mA	P_5.3.4
$I_{q} = I_{l} - I_{Q}$	,					$T_{\rm j}$ = 25 °C	
Current Consumption	$I_{q}$	_	62	77	μΑ	$I_{\rm Q}$ = 0.05 mA	P_5.3.7
$I_{q} = I_{l} - I_{Q}$	,					$T_{\rm j}$ < 125 °C	
Current Consumption	$I_{q}$	_	62	82	μΑ	$^{1)}I_{Q}$ = 500 mA	P_5.3.11
$I_{q} = I_{l} - I_{Q}$						$T_{\rm j}$ < 125 °C	

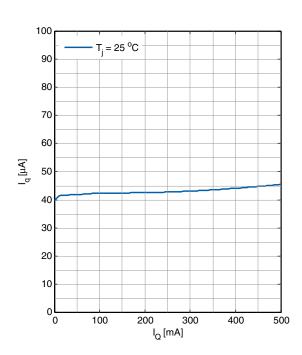
<sup>1)</sup> Not subject to production test, specified by design



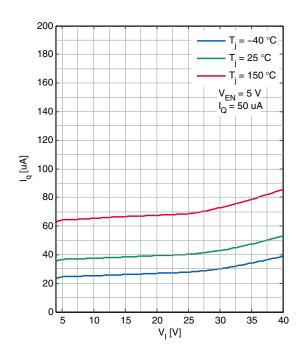
## **5.4** Typical Performance Characteristics Current Consumption

## **Typical Performance Characteristics**

# Current Consumption $I_{\rm q}$ versus Output Current $I_{\rm Q}$



# Current Consumption $I_{\rm q}$ versus Input Voltage $V_{\rm l}$





## 5.5 Enable

The TLS850D0TE can be switched on and off by the Enable feature: Connect a HIGH level as specified below (e.g. the battery voltage) to pin EN to enable the device; connect a LOW level as specified below (e.g. GND) to shut it down. The enable has a built in hysteresis to avoid toggling between ON/OFF state, if signals with slow slopes are applied to the EN input.

#### **Table 7** Electrical Characteristics Enable

 $T_{\rm j}$  = -40 °C to +150 °C,  $V_{\rm l}$  = 13.5 V, all voltages with respect to ground (unless otherwise specified) Typical values are given at  $T_{\rm j}$  = 25 °C

Parameter	Symbol		Values	3	Unit	Note / Test Condition	Number
		Min.	Тур.	Max.			
High Level Input Voltage	$V_{EN,H}$	2	_	_	V	$V_{\mathrm{Q}}$ settled	P_5.5.1
Low Level Input Voltage	$V_{EN,L}$	-	_	8.0	V	V <sub>Q</sub> ≤ 0.1 V	P_5.5.2
Enable Threshold Hysteresis	$V_{EN,Hy}$	100	_	_	mV	_	P_5.5.3
High Level Input Current	$I_{EN,H}$	_	_	3.5	μΑ	V <sub>EN</sub> = 3.3 V	P_5.5.4
High Level Input Current	$I_{EN,H}$	_	_	22	μA	V <sub>EN</sub> ≤ 18 V	P_5.5.6
Enable internal pull-down resistor	$R_{EN}$	0.95	1.5	2.6	ΜΩ	_	P_5.5.7

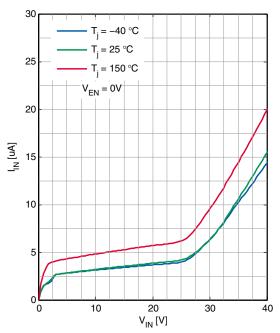
Data Sheet 18 Rev. 1.0, 2016-10-07



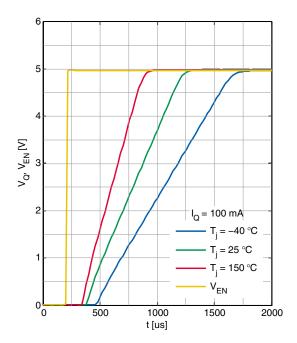
## 5.6 Typical Performance Characteristics Enable

## **Typical Performance Characteristics**

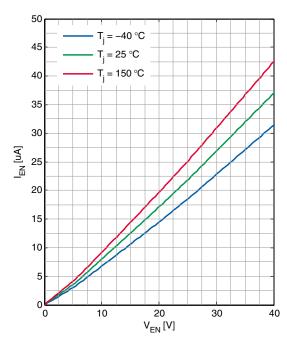
Input Current  $I_{\rm IN}$  versus Input Voltage  $V_{\rm IN}$  (condition:  $V_{\rm EN}$  = 0 V)



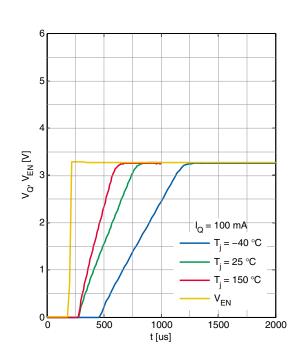
Output Voltage  $V_{\rm Q}$  versus time (EN switched ON, 5 V version)



## Enabled Input Current $I_{\mathrm{EN}}$ versus Enabled Input Voltage $V_{\mathrm{EN}}$



Output Voltage  $V_{\rm Q}$  versus time (EN switched ON, 3.3 V version)





## 5.7 Reset

The TLS850D0TE's output voltage is supervised by the Reset feature, including Undervoltage Reset and delayed Reset at Power-On.

The Undervoltage Reset function sets the pin RO to LOW, in case  $V_{\rm Q}$  is falling for any reason below the Reset Threshold  $V_{\rm RT.low}$ .

When the regulator is powered on, the pin RO is held at LOW for the duration of the Power-On Reset Delay Time  $t_{\rm rd}$ .

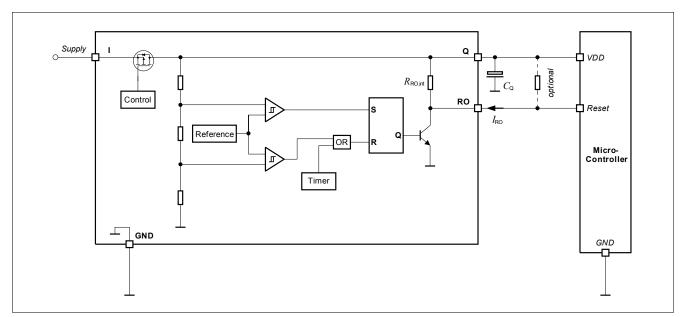


Figure 6 Block Diagram Reset Circuit

## **Reset Delay Time**

The Reset Delay Time  $t_{rd}$  is fix defined according to **Table 8**.

## Table 8 Reset DelayTime

Reset delay timing	$t_{\sf rd}$
fix	16.5 ms

### **Power-On Reset Delay Time**

The power-on reset delay time is defined by the parameter  $t_{rd}$  and allows a microcontroller and oscillator to start up. This delay time is the time period from exceeding the upper reset switching threshold  $V_{\rm RT,high}$  until the reset is released by switching the reset output "RO" from "LOW" to "HIGH".

### **Undervoltage Reset Delay Time**

Unlike the power-on reset delay time, the undervoltage reset delay time is defined by the parameter  $t_{rd}$  and considers an output undervoltage event where the output voltage  $V_{Q}$  trigger the  $V_{RT,low}$  threshold.

#### **Reset Blanking Time**

The reset blanking time  $t_{\text{rr.blank}}$  avoids that short undervoltage spikes trigger an unwanted reset "low" signal.



#### **Reset Reaction Time**

In case the output voltage of the regulator drops below the output undervoltage lower reset threshold  $V_{\rm RT,low}$ , the reset output "RO" is set to low, after the delay of the internal reset reaction time  $t_{\rm rr,int}$ . The reset blanking time  $t_{\rm rr,blank}$  is part of the reset reaction time  $t_{\rm rr,int}$ .

### Reset Output "RO"

The reset output "RO" is an open collector output with an integrated pull-up resistor. In case a lower-ohmic "RO" signal is desired, an external pull-up resistor can be connected to the output "Q". Since the maximum "RO" sink current is limited, the minimum value of the optional external resistor " $R_{RO,ext}$ " is given in **Table** "**Reset Output RO**" on Page 22.

## Reset Output "RO" Low for VQ ≥ 1 V

In case of an undervoltage reset condition reset output "RO" is held "low" for  $V_{\rm Q} \ge$  1 V, even if the input "I" is not supplied and the voltage  $V_{\rm I}$  drops below 1 V. This is achieved by supplying the reset circuit from the output capacitor.

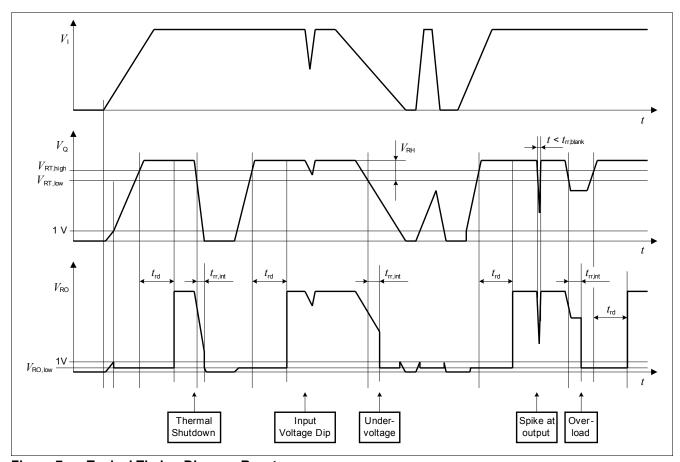


Figure 7 Typical Timing Diagram Reset

Data Sheet 21 Rev. 1.0, 2016-10-07



## Table 9 Electrical Characteristics Reset

 $T_{\rm j}$  = -40 °C to +150 °C,  $V_{\rm l}$  = 13.5 V, all voltages with respect to ground (unless otherwise specified) Typical values are given at  $T_{\rm i}$  = 25 °C

Parameter	Symbol	ol Value:		S	Unit	Note / Test Condition	Number
		Min.	Тур.	Max.	1		
Output Undervoltage Reset 5V Vo	ersion only	,			"	· ·	1
Output Undervoltage Reset Upper Switching Threshold	$V_{ m RT,high}$	4.6	4.7	4.8	V	$V_{Q}$ increasing	P_5.7.1
Output Undervoltage Reset Lower Switching Threshold - Default	$V_{RT,low}$	4.5	4.6	4.7	V	$V_{ m Q}$ decreasing	P_5.7.2
Output Undervoltage Reset Switching Hysteresis	$V_{RT,hy}$	60	100	_	mV	_	P_5.7.3
Output Undervoltage Reset Headroom $V_{\rm Q}$ - $V_{\rm RT}$	$V_{RH}$	200	400	_	mV	_	P_5.7.4
Output Undervoltage Reset 3V3 \	ersion on	ly	•	•	'		1
Output Undervoltage Reset Upper Switching Threshold	$V_{\mathrm{RT,high}}$	3.08	3.15	3.22	V	$V_{ m Q}$ increasing	P_5.7.5
Output Undervoltage Reset Lower Switching Threshold - Default	$V_{\mathrm{RT,low}}$	3.0	3.05	3.13	V	$V_{\mathrm{Q}}$ decreasing	P_5.7.6
Output Undervoltage Reset Switching Hysteresis	$V_{RT,hy}$	60	100	_	mV	_	P_5.7.7
Output Undervoltage Reset Headroom $V_{\rm Q}$ - $V_{\rm RT}$	$V_{RH}$	100	250	_	mV	_	P_5.7.8
Reset Output RO	-1	'	•	•	'		1
Reset Output Low Voltage	$V_{RO,low}$	-	0.2	0.4	V	1 V $\leq V_{\rm Q} \leq V_{\rm RT}$ ; $R_{\rm RO} \geq 5.1 \text{ k}\Omega$	P_5.7.40
Reset Output Internal Pull-Up Resistor	$R_{RO,int}$	13	20	36	kΩ	internally connected to Q	P_5.7.41
Reset Output External Pull-up Resistor to $V_{\rm Q}$	$R_{RO,ext}$	5.1	_	_	kΩ	$ 1 \ V \le V_{Q} \le V_{RT}  ; $ $V_{RO} \le 0.4 \ V $	P_5.7.42
Reset Delay Timing		"	1		"	·	1
Reset Delay Time	$t_{\rm rd}$	13.2	16.5	19.8	ms	Fixed Timing	P_5.7.44
Reset blanking time	t <sub>rr,blank</sub>	_	6	_	μs	<sup>1)</sup> for $V_{\rm Q,nom}$ = 3.3 V	P_5.7.22
Reset blanking time	t <sub>rr,blank</sub>	_	7	_	μs	$^{2)}$ for $V_{\rm Q,nom}$ = 5 V	P_5.7.46
Internal Reset Reaction Time	$t_{\rm rr,int}$	_	7	20	μs	for $V_{\rm Q,nom}$ = 3.3 V	P_5.7.23
Internal Reset Reaction Time	$t_{\rm rr,int}$	_	10	33	μs	for $V_{\rm Q,nom}$ = 5 V	P_5.7.36

<sup>1)</sup> Not subject to production test, specified by design.

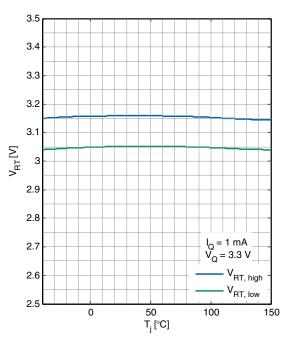
<sup>2)</sup> Not subject to production test, specified by design.



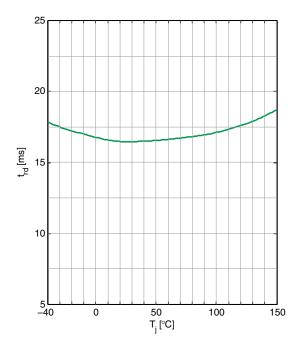
## 5.8 Typical Performance Characteristics Reset

## **Typical Performance Characteristics**

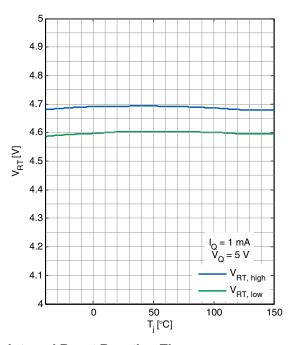
# Undervoltage Reset Threshold $V_{\rm RT}$ versus Junction Temperature $T_{\rm i}$ (3.3 V version)



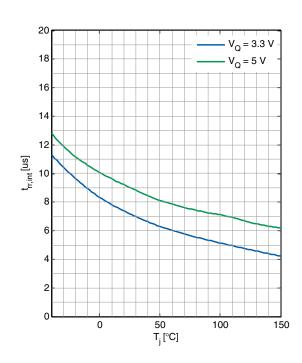
## Power On Reset Delay Time $t_{\rm rd}$ versus Junction Temperature $T_{\rm i}$



# Undervoltage Reset Threshold $V_{\rm RT}$ versus Junction Temperature $T_{\rm i}$ (5 V version)



Internal Reset Reaction Time  $t_{\rm rr,int}$  versus Junction Temperature  $T_{\rm j}$ 





**Application Information** 

## 6 Application Information

## 6.1 Application Diagram

Note: The following information is given as a hint for the implementation of the device only and shall not be regarded as a description or warranty of a certain functionality, condition or quality of the device.

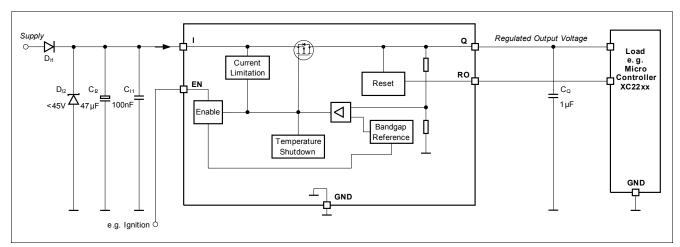


Figure 8 Application Diagram

Note: This is a very simplified example of an application circuit. The function must be verified in the real application.

#### 6.2 Selection of External Components

## 6.2.1 Input Pin

The typical input circuitry for a linear voltage regulator is shown in the application diagram above.

A ceramic capacitor at the input, in the range of 100 nF to 470 nF, is recommended to filter out the high frequency disturbances imposed by the line e.g. ISO pulses 3a/b. This capacitor must be placed very close to the input pin of the linear voltage regulator on the PCB.

An aluminum electrolytic capacitor in the range of 10  $\mu$ F to 470  $\mu$ F is recommended as an input buffer to smooth out high energy pulses, such as ISO pulse 2a. This capacitor should be placed close to the input pin of the linear voltage regulator on the PCB.

An overvoltage suppressor diode can be used to further suppress any high voltage beyond the maximum rating of the linear voltage regulator and protect the device against any damage due to over-voltage.

The external components at the input are not mandatory for the operation of the voltage regulator, but they are recommended in case of possible external disturbances.

## 6.2.2 Output Pin

An output capacitor is mandatory for the stability of linear voltage regulators.

The requirement to the output capacitor is given in "Functional Range" on Page 8. The graph "Output Capacitor Series Resistor ESR(CQ) versus Output Current IQ" on Page 15 shows the stable operation range of the device.



### **Application Information**

TLS850D0TE is designed to be also stable with low ESR capacitors. According to the automotive requirements, ceramic capacitors with X5R or X7R dielectrics are recommended.

The output capacitor should be placed as close as possible to the regulator's output and GND pins and on the same side of the PCB as the regulator itself.

In case of rapid transients of input voltage or load current, the capacitance should be dimensioned in accordance and verified in the real application that the output stability requirements are fulfilled.

### 6.3 Thermal Considerations

Knowing the input voltage, the output voltage and the load profile of the application, the total power dissipation can be calculated:

$$P_{\rm D} = (V_{\rm I} - V_{\rm Q}) \times I_{\rm Q} + V_{\rm I} \times I_{\rm Q} \tag{1}$$

with

- $P_{\rm D}$ : continuous power dissipation
- V<sub>1</sub>: input voltage
- $V_{\rm O}$ : output voltage
- I<sub>O</sub>: output current
- $I_a$ : quiescent current

The maximum acceptable thermal resistance  $R_{th,JA}$  can then be calculated:

$$R_{\text{thJA,max}} = \left( T_{\text{j,max}} - T_{\text{a}} \right) / P_{\text{D}}$$
 (2)

with

- T<sub>i.max</sub>: maximum allowed junction temperature
- T<sub>a</sub>: ambient temperature

Based on the above calculation the proper PCB type and the necessary heat sink area can be determined with reference to the specification in "Thermal Resistance" on Page 9.

### Example

Application conditions:

$$V_{\rm I}$$
 = 13.5 V  $V_{\rm Q}$  = 5 V  $I_{\rm Q}$  = 175 mA  $T_{\rm a}$  = 85 °C

Calculation of  $R_{\text{thJA.max}}$ :

$$\begin{split} P_{\rm D} &= (V_{\rm I} - V_{\rm Q}) \times I_{\rm Q} + V_{\rm I} \times I_{\rm q} & (V_{\rm I} \times I_{\rm q} \text{ can be neglected because of very low } I_{\rm q}) \\ &= (13.5 \text{ V} - 5 \text{ V}) \times 175 \text{ mA} \\ &= 1.487 \text{ W} \\ R_{\rm thJA,max} &= (T_{\rm j,max} - T_{\rm a}) \ / \ P_{\rm D} \\ &= (150 \ ^{\circ}{\rm C} - 85 \ ^{\circ}{\rm C}) \ / \ 1.487 \ {\rm W} = 43.71 \ {\rm K/W} \end{split}$$